HIGH DIODE

SBDD20100CT

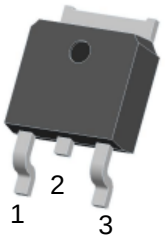
TO-252-2L Plastic-Encapsulate Diodes

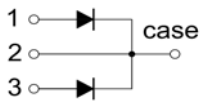
Schottky Rectifier

MAIN CHARACTERISTICS

I_O	20（2×10）A
V_{RRM}	100 V
T_j	150 ℃
$V_{F(typ)}$	0.67V （@Ta=125℃）

TO-252-2L

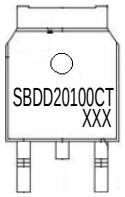




FEATURES

- Low Power Loss,High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop

MARKING



XXX=Date Code

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak repetitive reverse voltage	100	V
V_{RWM}	Working peak reverse voltage		
V_R	DC blocking voltage		
$V_{R(RMS)}$	RMS reverse voltage	70	V
I_O	Average rectified output current	20	A
I_{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)	300	A
P_D	Power dissipation	2.5	W
$R_{\Theta JA}$	Thermal resistance from junction to ambient	50.0	℃/W
T_j	Junction temperature	150	℃
T_{stg}	Storage temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=0.1mA		100			V
Reverse current	I_R	V_R=100V	Tj =25℃		1	10	uA
			Tj =125℃		0.7		mA
Forward voltage	V_F	I_F=5A	Tj =25℃		0.72		V
			Tj =125℃		0.61		V
		I_F=10A	Tj =25℃		0.79	0.85	V
			Tj =125℃		0.67		V

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

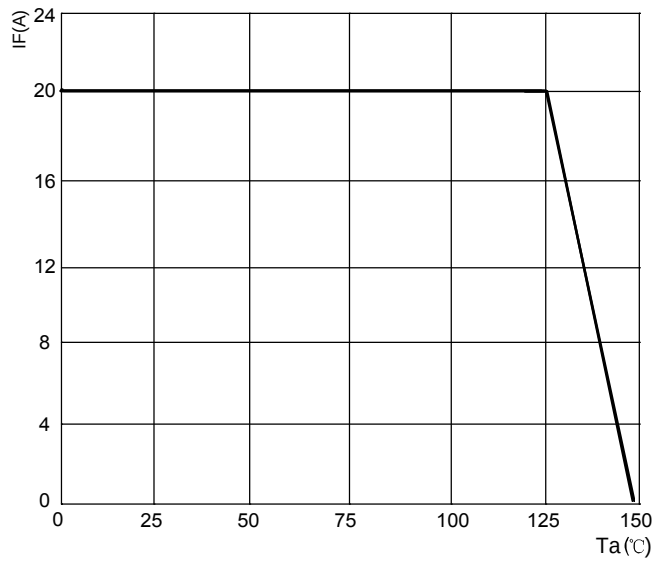


FIG.2: TYPICAL FORWARD CHARACTERISTICS

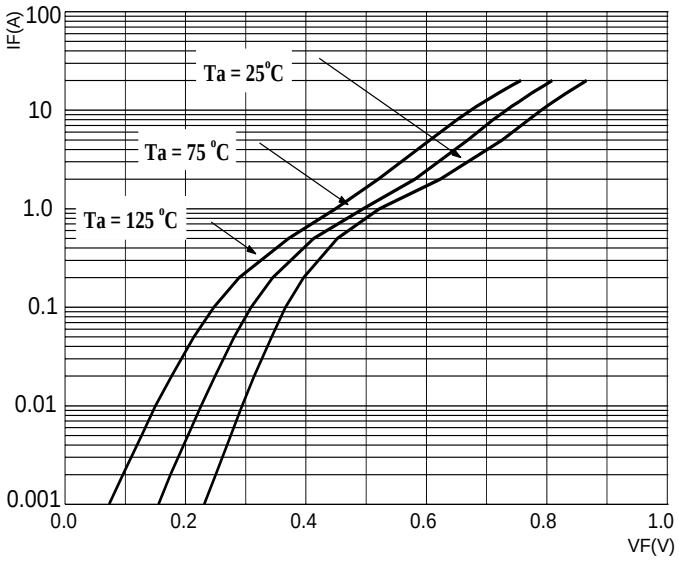


FIG.3: TOTAL CAPACITANCE DERATING CURVE

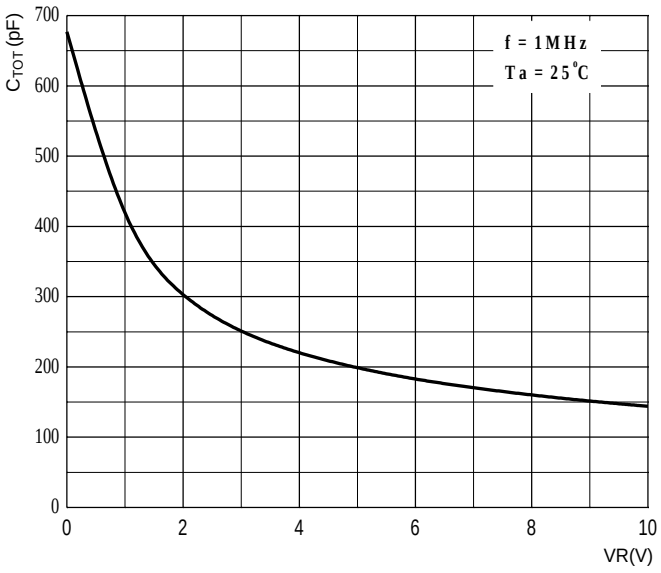
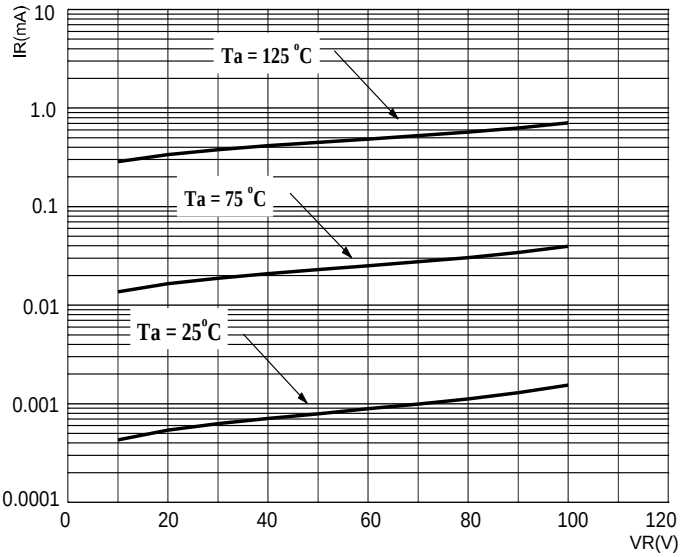
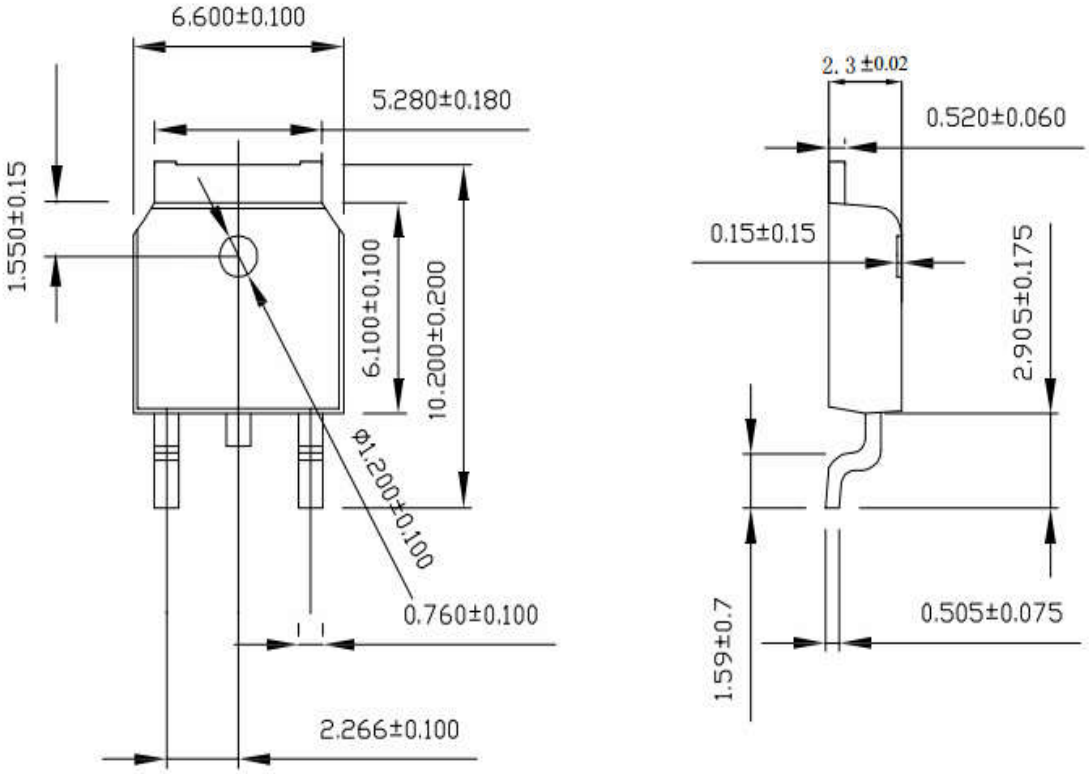


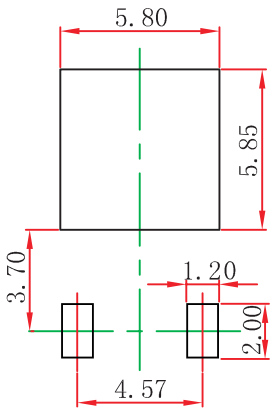
FIG.4: TYPICAL REVERSE CHARACTERISTICS



TO-252-2L Package Outline Dimensions



TO-252-2L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

NOTICE

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